InGaN Light-Emitting Diodes onc-Face Sapphire Range

Applied Physics Express

6, 111004

DOI: 10.7567/apex.6.111004

Citation Report

#	Article	IF	Citations
1	Detailed optical and electrical characterisation of green — Orange InGaN/GaN LEDs grown by MOVPE. , 2014, , .		0
2	Enhancing the quantum efficiency of InGaN yellow-green light-emitting diodes by growth interruption. Applied Physics Letters, 2014, 105, .	1.5	41
3	Monolithic white light emitting diodes using a (Ga,In)N-based light converter. , 2014, , .		1
4	The properties of reversed polarization yellow InGaN-GaN MQWs in p-side down structure grown by metalâ€"organic chemical vapor deposition on sapphire substrate. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 64, 57-62.	1.3	5
5	Realization of high-luminous-efficiency InGaN light-emitting diodes in the â€œgreen gapâ€•range. Scientific Reports, 2015, 5, 10883.	1.6	96
6	Effect of localization states on the electroluminescence spectral width of blueâ€"green light emitting InGaN/GaN multiple quantum wells. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	16
7	Internal quantum efficiency in yellow-amber light emitting AlGaN-InGaN-GaN heterostructures. Applied Physics Letters, 2015, 107, .	1.5	36
8	Effect of the design of the active region of monolithic multi-color LED heterostructures on their spectra and emission efficiency. Semiconductors, 2015, 49, 1516-1521.	0.2	3
9	Thermally Engineered Flip-Chip InGaN/GaN Well-Ordered Nanocolumn Array LEDs. IEEE Photonics Technology Letters, 2015, 27, 2343-2346.	1.3	6
10	On the increased efficiency in InGaN-based multiple quantum wells emitting at 530â€"590 nm with AlGaN interlayers. Journal of Crystal Growth, 2015, 415, 57-64.	0.7	46
11	Optimal ways of colour mixing for highâ€•quality whiteâ€•light LED sources. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 914-919.	0.8	40
12	Advantages of IIIâ€•nitride laser diodes in solidâ€•state lighting. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 980-985.	0.8	75
13	Photoluminescence behavior of amber light emitting GaInN-GaN heterostructures. Proceedings of SPIE, 2015, , .	0.8	0
14	Strain-compensated (Ga,In)N/(Al,Ga)N/GaN multiple quantum wells for improved yellow/amber light emission. Applied Physics Letters, 2015, 106, .	1.5	45
15	Carrier localization in In-rich InGaN/GaN multiple quantum wells for green light-emitting diodes. Scientific Reports, 2015, 5, 9373.	1.6	86
16	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. Journal of Crystal Growth, 2015, 425, 393-397.	0.7	8
17	Yellowâ€"red emission from (Ga,In)N heterostructures. Journal Physics D: Applied Physics, 2015, 48, 403001.	1.3	78
18	Localization effect in green light emitting InGaN/GaN multiple quantum wells with varying well thickness. Journal of Alloys and Compounds, 2015, 625, 266-270.	2.8	32

#	Article	IF	Citations
19	High luminous efficacy green light-emitting diodes with AlGaN cap layer. Optics Express, 2016, 24, 17868.	1.7	74
20	Performance enhancement of blue light-emitting diodes with InGaN/GaN multi-quantum wells grown on Si substrates by inserting thin AlGaN interlayers. Journal of Applied Physics, 2016, 120, .	1.1	29
22	Investigation of amber light-emitting diodes based on InGaN/AlN/AlGaN quantum wells. Japanese Journal of Applied Physics, 2016, 55, 05FJ06.	0.8	8
23	The microstructure of non-polar a-plane (112Â¯0) InGaN quantum wells. Journal of Applied Physics, 2016, 119, .	1.1	22
24	Green semipolar III-nitride light-emitting diodes grown by limited area epitaxy. Applied Physics Letters, 2016, 109, .	1.5	10
25	Auger effect in yellow light emitters based on InGaNâ€“AlGaNâ€“GaN quantum wells. Japanese Journal of Applied Physics, 2016, 55, 05FG10.	0.8	7
26	Temperature-dependent recombination coefficients in InGaN light-emitting diodes: Hole localization, Auger processes, and the green gap. Applied Physics Letters, 2016, 109, .	1.5	79
27	Highly stable and efficient green luminescent CdS colloidal nanocrystals. Journal of Nanophotonics, 2016, 10, 026017.	0.4	5
28	Investigation of NH3input partial pressure for N-polarity InGaN growth on GaN substrates by tri-halide vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA01.	0.8	6
29	Enhanced light output power of InGaN-based amber LEDs by strain-compensating AlN/AlGaN barriers. Journal of Crystal Growth, 2016, 448, 105-108.	0.7	46
30	Comparative study of (0001) and $(11ar{2}2)$ InGaN based light emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ10.	0.8	7
31	Influences of Si-doped graded short-period superlattice on green InGaN/GaN light-emitting diodes. Optics Express, 2016, 24, 7743.	1.7	26
32	Single-Layer Halide Perovskite Light-Emitting Diodes with Sub-Band Gap Turn-On Voltage and High Brightness. Journal of Physical Chemistry Letters, 2016, 7, 4059-4066.	2.1	175
33	Efficiency studies on semipolar GaInN-GaN quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 3117-3121.	0.8	5
34	Impact of Radiative and Nonradiative Recombination Processes on the Efficiency-Droop Phenomenon in InxGa1â^'xN Single Quantum Wells Studied by Scanning Near-Field Optical Microscopy. Physical Review Applied, 2016, 6, .	1.5	14
35	Decomposition of supercritical ammonia and modeling of supercritical ammoniaâ€“nitrogenâ€“hydrogen solutions with applicability toward ammonothermal conditions. Journal of Supercritical Fluids, 2016, 107, 17-30.	1.6	27
36	Light-emitting diodes for solid-state lighting: searching room for improvements. Proceedings of SPIE, 2016, , .	0.8	19
37	Optimized In composition and quantum well thickness for yellow-emitting (Ga,In)N/GaN multiple quantum wells. Journal of Crystal Growth, 2016, 434, 25-29.	0.7	6

#	Article	IF	Citations
38	Internal quantum efficiency and Auger recombination in green, yellow and red InGaN-based light emitters grown along the polar direction. Superlattices and Microstructures, 2017, 103, 245-251.	1.4	23
39	Ultraviolet, blue, and green InGaN-based light-emitting diodes functionalized with ZnO nanorods. Journal of Alloys and Compounds, 2017, 708, 612-618.	2.8	15
40	Effect of nanopillar sublayer embedded with SiO2 on deep traps in green GaN/InGaN light emitting diodes. Journal of Applied Physics, 2017, 121, .	1.1	10
41	Effect of small flow hydrogen treatment at the upper well/barrier interface on the properties of InGaN/GaN multiple quantum wells. Superlattices and Microstructures, 2017, 107, 293-298.	1.4	6
42	Fabrication of InGaN/GaN MQW nanoâ€LEDs by hydrogenâ€environment anisotropic thermal etching. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600613.	0.8	8
43	Green, Yellow, and Red LEDs. Topics in Applied Physics, 2017, , 239-266.	0.4	1
44	Development of Deep UV LEDs and Current Problems in Material and Device Technology. Semiconductors and Semimetals, 2017, 96, 45-83.	0.4	19
45	Effects of Wavelength and Defect Density on the Efficiency of (In,Ga)N-Based Light-Emitting Diodes. Physical Review Applied, 2017, 7, .	1.5	16
46	Flower-Like Internal Emission Distribution of LEDs with Monolithic Integration of InGaN-based Quantum Wells Emitting Narrow Blue, Green, and Red Spectra. Scientific Reports, 2017, 7, 7164.	1.6	5
47	Flower-like light distribution inside InGaN-based light-emitting diodes operated in spectral range from violet to red. , 2017, , .		0
48	Design and simulation to improve the structural efficiency of green light emission of GaN/InGaN/AlGaN light emitting diode. Frontiers of Optoelectronics, 2017, 10, 370-377.	1.9	3
49	Strain compensation in InGaN-based multiple quantum wells using AlGaN interlayers. AIP Advances, 2017, 7, .	0.6	36
50	Enhanced In incorporation in full InGaN heterostructure grown on relaxed InGaN pseudo-substrate. Applied Physics Letters, 2017, 110, .	1.5	96
51	Carrier localization in InGaN by composition fluctuations: implication to the â€œgreen gapâ€• Photonics Research, 2017, 5, A7.	3.4	47
52	Diffusion-Driven Charge Transport in Light Emitting Devices. Materials, 2017, 10, 1421.	1.3	8
53	Perspective: Toward efficient GaN-based red light emitting diodes using europium doping. Journal of Applied Physics, 2018, 123, .	1.1	100
54	Fundamental Limitations of Wide-Bandgap Semiconductors for Light-Emitting Diodes. ACS Energy Letters, 2018, 3, 655-662.	8.8	48
55	The influence of well thickness on the photoluminescence properties of blue-violet light emitting InGaN/GaN multiple quantum wells. Superlattices and Microstructures, 2018, 113, 534-540.	1.4	5

#	Article	IF	Citations
56	Influence of in doping in GaN barriers on luminescence properties of InGaN/GaN multiple quantum well LEDs. Superlattices and Microstructures, 2018, 114, 32-36.	1.4	6
57	Quantitative study of energy-transfer mechanism in Eu,O-codoped GaN by time-resolved photoluminescence spectroscopy. Journal of Applied Physics, 2018, 123, 161419.	1.1	4
58	Optical properties of InGaN thin films in the entire composition range. Journal of Applied Physics, 2018, 123, .	1.1	37
59	Efficiency enhancement of InGaN amber MQWs using nanopillar structures. Nanophotonics, 2018, 7, 317-322.	2.9	10
60	Effects of Introduction of InGaN Quantum Structures on Structural and Optical Properties of InGaN Nanocolumns. Physica Status Solidi (B): Basic Research, 2018, 255, 1700481.	0.7	1
61	Thickness Study of Er-Doped Magnesium Zinc Oxide Diode by Spray Pyrolysis. Crystals, 2018, 8, 454.	1.0	3
62	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. Journal of Applied Physics, 2018, 124, .	1.1	27
63	Integrating AlInN interlayers into InGaN/GaN multiple quantum wells for enhanced green emission. Applied Physics Letters, 2018, 112, .	1.5	29
64	Development of high performance green c-plane III-nitride light-emitting diodes. Optics Express, 2018, 26, 5591.	1.7	47
65	Performance enhancement of yellow InGaN-based multiple-quantum-well light-emitting diodes grown on Si substrates by optimizing the InGaN/GaN superlattice interlayer. Optical Materials Express, 2018, 8, 1221.	1.6	25
66	Influence of stress on the optical properties of double InGaN/GaN multiple quantum wells. Optical Materials Express, 2018, 8, 1528.	1.6	3
67	Effect of Carrier Localization on Recombination Processes and Efficiency of InGaN-Based LEDs Operating in the â€œGreen Gapâ€• Applied Sciences (Switzerland), 2018, 8, 818.	1.3	24
68	Evaluation of Light Extraction Efficiency of GaN-Based Nanorod Light-Emitting Diodes by Averaging over Source Positions and Polarizations. Crystals, 2018, 8, 27.	1.0	18
69	Study on the Coupling Mechanism of the Orthogonal Dipoles with Surface Plasmon in Green LED by Cathodoluminescence. Nanomaterials, 2018, 8, 244.	1.9	6
70	Infrared emitters using III-nitride semiconductors. , 2018, , 587-617.		3
71	IIIâ€Nitride Microâ€LEDs for Efficient Emissive Displays. Laser and Photonics Reviews, 2019, 13, 1900141.	4.4	93
72	Optimization of indium tin oxide layer thickness for surface-plasmon-enhanced green light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SCCC27.	0.8	4
73	Growth and characterization of In Ga1âˆ’N (0â€¯<â€¯xâ€¯<â€¯0.16) templates for controlled emissions from MQW. Journal of Crystal Growth, 2019, 520, 18-26.	0.7	14

#	Article	IF	Citations
74	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaN-based multiple quantum wells using rate equations of exciton recombination. Japanese Journal of Applied Physics, 2019, 58, SCCB02.	0.8	11
75	High-luminous efficacy green light-emitting diodes with InGaN/GaN quasi-superlattice interlayer and Al-doped indium tin oxide film. Journal of Alloys and Compounds, 2019, 794, 137-143.	2.8	16
76	Tuning the Resonant Frequency of a Surface Plasmon by Double-Metallic Ag/Au Nanoparticles for High-Efficiency Green Light-Emitting Diodes. Applied Sciences (Switzerland), 2019, 9, 305.	1.3	8
77	Temperature dependence of the color rendering index of a phosphor-conversion white light-emitting diode. AIP Advances, 2019, 9, .	0.6	2
78	InGaN Platelets: Synthesis and Applications toward Green and Red Light-Emitting Diodes. Nano Letters, 2019, 19, 2832-2839.	4.5	34
79	Enhanced Device Performance of GaInN-Based Green Light-Emitting Diode with Sputtered AlN Buffer Layer. Applied Sciences (Switzerland), 2019, 9, 788.	1.3	10
80	Recombination rates in green-yellow InGaN-based multiple quantum wells with AlGaN interlayers. Journal of Applied Physics, 2019, 126, .	1.1	12
81	On the Carrier Transport for InGaN/GaN Core-Shell Nanorod Green Light-Emitting Diodes. IEEE Nanotechnology Magazine, 2019, 18, 176-182.	1.1	5
82	The AlGaInP/AlGaAs Material System and Red/Yellow LED. Solid State Lighting Technology and Application Series, 2019, , 171-202.	0.3	1
83	Abnormal Stranskiâ€“Krastanov Mode Growth of Green InGaN Quantum Dots: Morphology, Optical Properties, and Applications in Light-Emitting Devices. ACS Applied Materials & Interfaces, 2019, 11, 1228-1238.	4.0	51
84	InGaN based tunable green light-emitting diodes using InAlN interlayer and strain compensated AlGaN interlayer for better device performance. Optics and Laser Technology, 2020, 124, 105975.	2.2	6
85	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. Journal of Applied Physics, 2020, 127, 013102.	1.1	6
86	Design and growth of GaN-based blue and green laser diodes. Science China Materials, 2020, 63, 1348-1363.	3.5	32
87	Improving the internal quantum efficiency of QD/QW hybrid structures by increasing the GaN barrier thickness. RSC Advances, 2020, 10, 41443-41452.	1.7	2
88	Increasing the Luminescence Efficiency of Long-Wavelength (<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 207 Td (xmlns:mml="ht xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow>	1.5	2
89	Device quality templates of InxGa1â^'xN (x < 0.1) with defect densities comparable to GaN. Applied Physics Letters, 2020, 117, .	1.5	7
90	Green gap in GaN-based light-emitting diodes: in perspective. Critical Reviews in Solid State and Materials Sciences, 2021, 46, 450-467.	6.8	23
91	A 3D simulation comparison of carrier transport in green and blue c-plane multi-quantum well nitride light emitting diodes. Journal of Applied Physics, 2020, 128, 235703.	1.1	9

#	Article	IF	Citations
92	Observing relaxation in device quality InGaN templates by TEM techniques. Applied Physics Letters, 2020, 116, .	1.5	13
93	Electronic properties of dilute-As InGaNAs alloys: A first-principles study. Journal of Applied Physics, 2020, 127, .	1.1	2
94	Photoluminescence properties of InGaN/GaN multiple quantum wells containing a gradually changing amount of indium in each InGaN well layer along the growth direction. Journal of Luminescence, 2020, 223, 117225.	1.5	7
95	High external quantum efficiency III-nitride micro-light-emitting diodes. Semiconductors and Semimetals, 2021, 106, 95-121.	0.4	3
96	Performance Enhancement of InGaN/GaN Green QW LEDs with Different Interlayers and Doping in the Barriers. Lecture Notes in Networks and Systems, 2021, , 484-489.	0.5	0
97	Group-III-nitride and halide-perovskite semiconductor gain media for amplified spontaneous emission and lasing applications. Journal Physics D: Applied Physics, 2021, 54, 143001.	1.3	20
98	Performance improvement of green QW LEDs, for the different doping in the barriers, using InAlN interlayer and strain compensated AlGaN interlayer at the InGaN/GaN interface. Optical Materials, 2021, 113, 110863.	1.7	4
99	Strain-induced yellow to blue emission tailoring of axial InGaN/GaN quantum wells in GaN nanorods synthesized by nanoimprint lithography. Scientific Reports, 2021, 11, 6754.	1.6	7
100	Factors Affecting Surface Plasmon Coupling of Quantum Wells in Nitride-Based LEDs: A Review of the Recent Advances. Nanomaterials, 2021, 11, 1132.	1.9	5
101	Influence of low-temperature GaN-Cap layer thickness on the InGaN/GaN multiple quantum well structure and its luminescence. Optical Materials Express, 2021, 11, 1411.	1.6	2
102	Effect of Graded-Indium-Content Superlattice on the Optical and Structural Properties of Yellow-Emitting InGaN/GaN Quantum Wells. Materials, 2021, 14, 1877.	1.3	5
103	Step-type quantum wells with slightly varied InN composition for GaN-based yellow micro light-emitting diodes. Applied Optics, 2021, 60, 3006.	0.9	2
104	Multi-colour light emission from InGaN nanowires monolithically grown on Si substrate by MBE. Nanotechnology, 2021, 32, 335604.	1.3	9
105	Structure and luminescence properties of Eu3+ and Dy3+ implanted GaN films. Superlattices and Microstructures, 2021, 156, 106974.	1.4	3
106	Realization of III-Nitride c-Plane microLEDs Emitting from 470 to 645 nm on Semi-Relaxed Substrates Enabled by V-Defect-Free Base Layers. Crystals, 2021, 11, 1168.	1.0	6
107	Recombination Rates of In_xGa_{1â^'x}N/Al_yGa_{1â^'y}N/GaN Multiple Quantum Wells Emitting From 640 to 565 nm. IEEE Journal of Quantum Electronics, 2021, 57, 1-7.	1.0	2
108	n-type GaN surface etched green light-emitting diode to reduce non-radiative recombination centers. Applied Physics Letters, 2021, 118, .	1.5	14
109	Recent progress in nonpolar and semi-polar GaN light emitters on patterned Si substrates. , 2018, , .		3

#	Article	IF	Citations
110	Improving carrier transport in AlGaN deep-ultraviolet light-emitting diodes using a strip-in-a-barrier structure. Applied Optics, 2020, 59, 5276.	0.9	20
111	Enhanced hole transport in AlGaN deep ultraviolet light-emitting diodes using a double-sided step graded superlattice electron blocking layer. Journal of the Optical Society of America B: Optical Physics, 2020, 37, 2564.	0.9	9
112	Ultrapure and highly efficient green light emitting devices based on ligand-modified CsPbBr₃ quantum dots. Photonics Research, 2020, 8, 1086.	3.4	51
113	Efficient InGaN-based yellow-light-emitting diodes. Photonics Research, 2019, 7, 144.	3.4	124
114	Semiconductor yellow light-emitting diodes. Wuli Xuebao/Acta Physica Sinica, 2019, 68, 168503.	0.2	3
115	III-Nitride Light-Emitting Devices. Photonics, 2021, 8, 430.	0.9	18
116	Shifting LED emission from blue to the green gap spectral range using In0.12Ga0.88N relaxed templates. Superlattices and Microstructures, 2021, 160, 107065.	1.4	3
117	Efficiency enhancement of III-nitride light-emitting diodes with strain-compensated thin-barrier InGaN/AlN/GaN multiple quantum wells. OSA Continuum, 2019, 2, 1207.	1.8	7
118	Effect of InGaN growth interruption on photoluminescence properties of an InGaN-based multiple quantum well structure. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 119, 113982.	1.3	3
119	Patterned sapphire substrates cause a wavelength shift of green InGaN light-emitting diodes. Optical Materials Express, 2020, 10, 2045.	1.6	1
120	Near-Infrared Electroluminescence of AlGaN Capped InGaN Quantum Dots Formed by Controlled Growth on Photoelectrochemical Etched Quantum Dot Templates. Photonics Research, 0, , .	3.4	5
121	Investigation of Micromorphology and Carrier Recombination Dynamics for InGaN/GaN Multi-Quantum Dots Grown by Molecular Beam Epitaxy. Crystals, 2021, 11, 1312.	1.0	9
122	Enhanced P-Type GaN Conductivity by Mg Delta Doped AlGaN/GaN Superlattice Structure. Materials, 2021, 14, 144.	1.3	6
123	Modulation and Refinement of Inâ€“N re-Bonding of InGaN Through in Post-Flow During a Refined Temper Fire Treatment Process. IEEE Access, 2020, 8, 224433-224438.	2.6	0
124	InGaN-Based microLED Devices Approaching 1% EQE with Red 609 nm Electroluminescence on Semi-Relaxed Substrates. Crystals, 2021, 11, 1364.	1.0	30
125	Temporally modulated energy shuffling in highly interconnected nanosystems. Nanophotonics, 2020, 10, 851-876.	2.9	5
126	Modeling of In0.17Ga0.83N/InxGa1â€“xN/AlyGa1â€“yN light emitting diode structure on ScAlMgO4 (0001) substrate for high intensity red emission. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2020, 23, 408-414.	0.3	1
127	Greatly suppressed potential inhomogeneity and performance improvement of c-plane InGaN green laser diodes. Science China Materials, 2022, 65, 543-546.	3.5	8

#	Article	IF	Citations
128	Optical Properties of GaN-Based Green Light-Emitting Diodes Influenced by Low-Temperature p-GaN Layer. Nanomaterials, 2021, 11, 3134.	1.9	1
129	Delta InN-InGaN Quantum Wells With AlGaN Interlayers for Long Wavelength Emission. IEEE Journal of Quantum Electronics, 2022, 58, 1-6.	1.0	1
130	Dilute-As InGaNAs/GaN Quantum Wells for High-Efficiency Red Emitters. IEEE Journal of Quantum Electronics, 2022, 58, 1-6.	1.0	1
131	Effect of low-temperature interlayer in active-region upon photoluminescence in multiple-quantum-well InGaN/GaN. Journal of Luminescence, 2022, 244, 118741.	1.5	3
132	Photoluminescence Study of Carrier Localization and Recombination in Nearly Strainâ€Balanced Nonpolar InGaN/AlGaN Quantum Wells. Physica Status Solidi (B): Basic Research, 0, , 2100569.	0.7	1
133	Structural and emission improvement of cyan-emitting InGaN quantum wells by introducing a large substrate misorientation angle. Optical Materials Express, 2022, 12, 119.	1.6	2
134	Reduction of V-pit density and depth in InGaN semibulk templates and improved LED performance with insertion of high temperature semibulk layers. Semiconductor Science and Technology, 2022, 37, 075003.	1.0	0
135	Cubic InxGa1â^'xN/GaN quantum wells grown by Migration Enhanced Epitaxy (MEE) and conventional Molecular Beam Epitaxy (MBE). Journal of Alloys and Compounds, 2022, 921, 165994.	2.8	4
136	Investigation into the stability condition of correlated color temperature of white illumination sources based on trichromatic light-emitting diodes. Displays, 2023, 76, 102358.	2.0	1
137	Recombination Rate Analysis of InGaN-Based Red-Emitting Light-Emitting Diodes. IEEE Journal of Quantum Electronics, 2023, 59, 1-9.	1.0	2
138	The effect of ammonia partial pressure on the growth of semipolar (11â€"22) InGaN/GaN MQWs and LED structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2023, 291, 116368.	1.7	1
139	An Ultrahigh Efficiency Excitonic Micro-LED. Nano Letters, 2023, 23, 1680-1687.	4.5	11
140	Application of nano-patterned InGaN fabricated by self-assembled Ni nano-masks in green InGaN/GaN multiple quantum wells. Journal of Semiconductors, 2023, 44, 042801.	2.0	1
141	Native defect clustering-induced carrier localization centers leading to a reduction of performance in Ga_{0.70}In_{0.30}N/GaN quantum wells. Optics Express, 2023, 31, 15779.	1.7	1